

Power Transistor (80V, 1A)

2SD1898 / 2SD1733 / 2SD1768S / 2SD1863

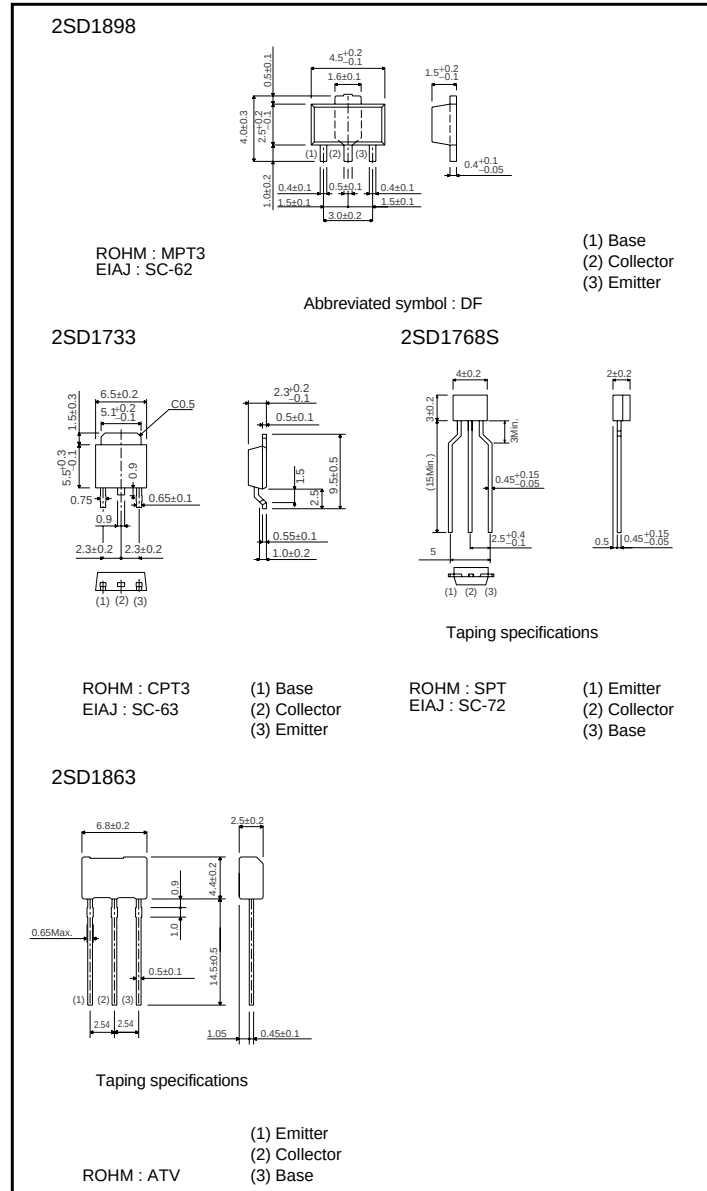
●Features

- 1) High V_{CE0} , $V_{CE0}=80V$
- 2) High I_c , $I_c=1A$ (DC)
- 3) Good h_{FE} linearity
- 4) Low V_{CE} (sat)
- 5) Complements the 2SB1260 / 2SB1241 / 2SB1181

●Structure

Epitaxial planer type
NPN silicon transistor

●External dimensions (Unit : mm)



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●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V _{CBO}	100	V
Collector-emitter voltage		V _{CEO}	80	V
Emitter-base voltage		V _{EBO}	5	V
Collector current		I _C	1	A (DC)
			2	A (Pulse)*1
Collector power dissipation	2SD1898	P _C	0.5	W
			2	W *3
	2SD1733		1	W
			10	W (T _C =25°C)
	2SD1768S		0.3	W
	2SD1863		1	W *2
Junction temperature		T _J	150	°C
Storage temperature		T _{stg}	−55 to +150	°C

*1 Pw=20ms, duty=1 / 2

*2 Printed circuit board 1.7mm thick, collector copper plating 1cm² or larger.

*3 When mounted on a 40×40×0.7mm ceramic board.

●Electrical characteristics (Ta=25°C)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage		BV_{CBO}	100	–	–	V	$I_C=50\mu A$
Collector-emitter breakdown voltage		BV_{CEO}	80	–	–	V	$I_C=1mA$
Emitter-base breakdown voltage		BV_{EBO}	5	–	–	V	$I_E=50\mu A$
Collector cutoff current		I_{CBO}	–	–	1	μA	$V_{CB}=80V$
Emitter cutoff current		I_{EBO}	–	–	1	μA	$V_{EB}=4V$
DC current transfer ratio	2SD1863	h_{FE}	180	–	390	–	$V_{CE}=3V, I_C=0.5A$ *
	2SD1733, 2SD1898		82	–	390	–	
	2SD1768S		120	–	390	–	
Collector-emitter saturation voltage		$V_{CE(sat)}$	–	0.15	0.4	V	$I_C/I_B=500mA/20mA$
Transition frequency		f_T	–	100	–	MHz	$V_{CE}=10V, I_E=-50mA, f=100MHz$
Output capacitance		C_{ob}	–	20	–	pF	$V_{CB}=10V, I_E=0A, f=1MHz$

* Measured using pulse current

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●Packaging specifications and h_{FE}

Type	h_{FE}	Package	Taping			
		Code	T100	TL	TP	TV2
		Basic ordering unit (pieces)	1000	2500	5000	2500
2SD1898	PQR		○	—	—	—
2SD1733	PQR		—	○	—	—
2SD1768S	QR		—	—	○	—
2SD1863	R		—	—	—	○

h_{FE} values are classified as follows :

Item	P	Q	R
h_{FE}	82~180	120~270	180~390

●Electrical characteristic curves

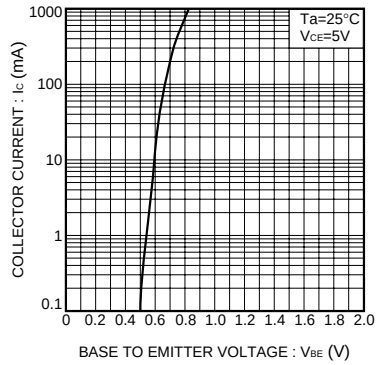


Fig.1 Grounded emitter propagation characteristics

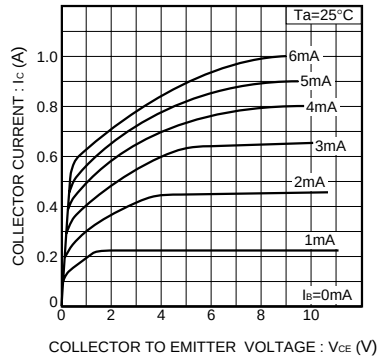


Fig.2 Grounded emitter output characteristics

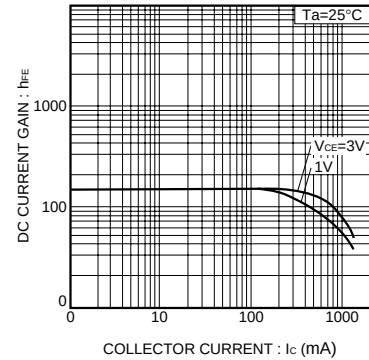


Fig.3 DC current gain vs. collector current

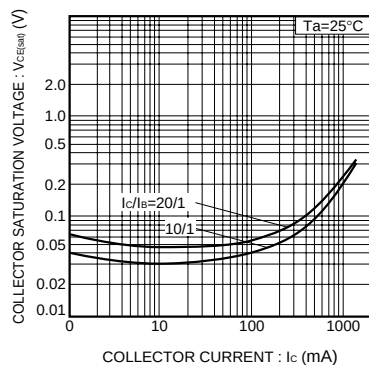


Fig.4 Collector-emitter saturation voltage vs. collector current

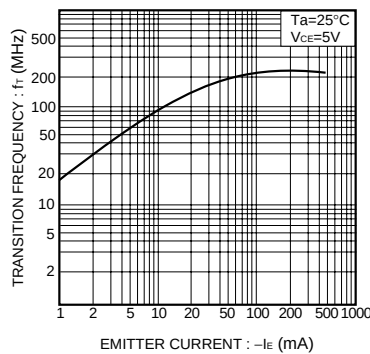


Fig.5 Gain bandwidth product vs. emitter current

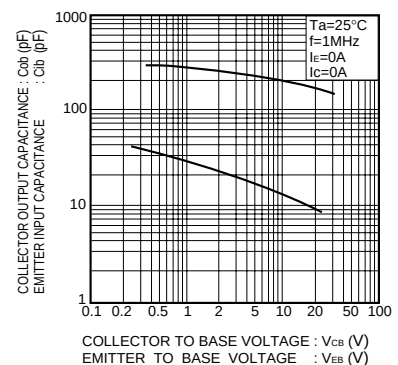


Fig.6 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

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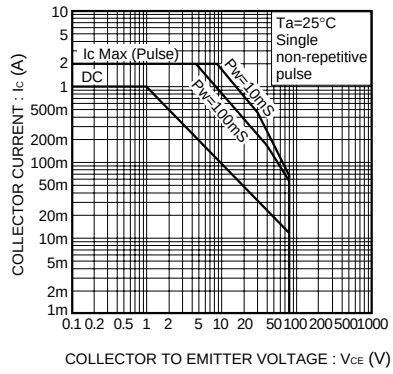


Fig.7 Safe operating area
(2SD1863)

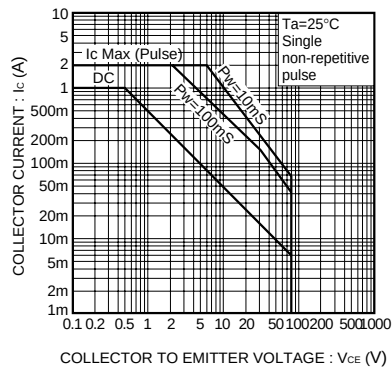


Fig.8 Safe operating area
(2SD1898)